

TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

1SS336

ULTRA HIGH SPEED SWITCHING APPLICATION.

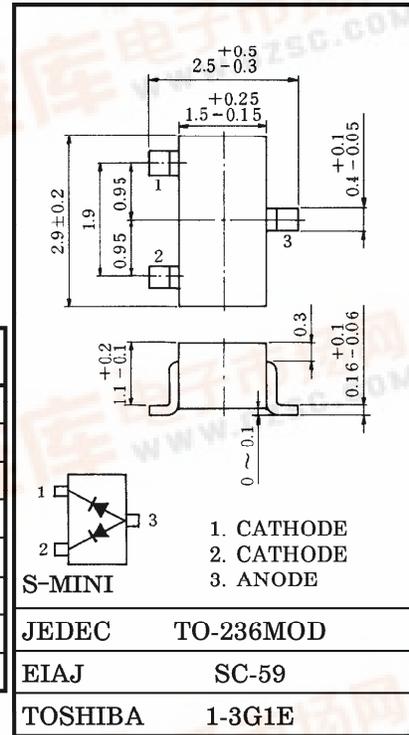
Unit in mm

- Small Package : SC-59
- Low Forward Voltage : $V_F(3) = 0.84V$ (Typ.)
- Fast Reverse Recovery Time : $t_{rr} = 7ns$ (Typ.)
- Small Total Capacitance : $C_T = 7pF$ (Typ.)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Maximum (Peak) Forward Current	I_{FM}	600*	mA
Average Forward Current	I_O	200*	mA
Surge Current (10ms)	I_{FSM}	6*	A
Power Dissipation	P	150	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55~150	$^\circ C$

* Unit Rating. Total Rating=Unit Rating×1.5

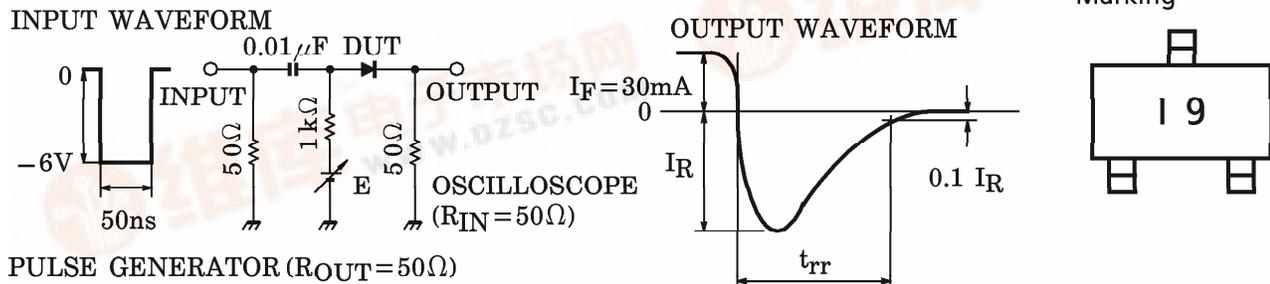


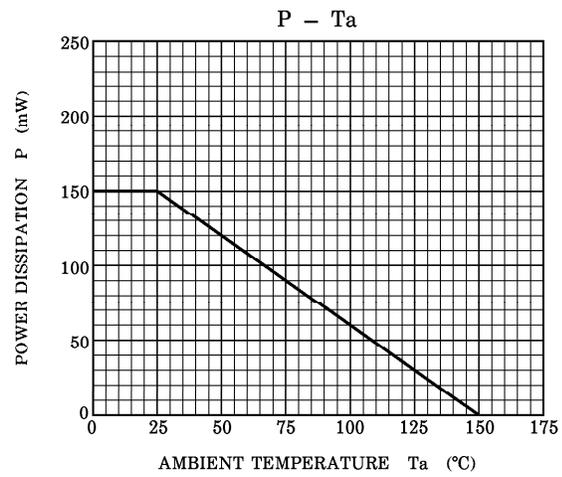
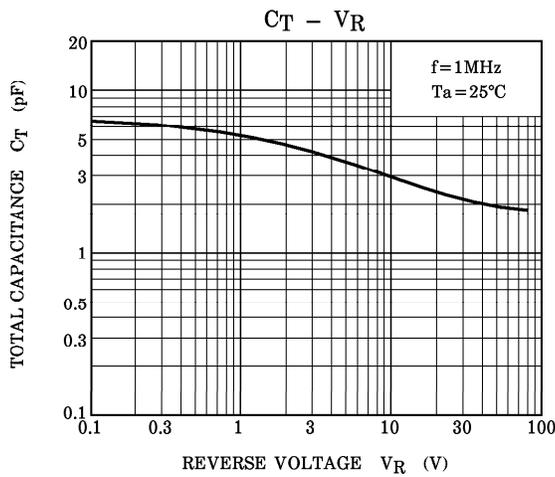
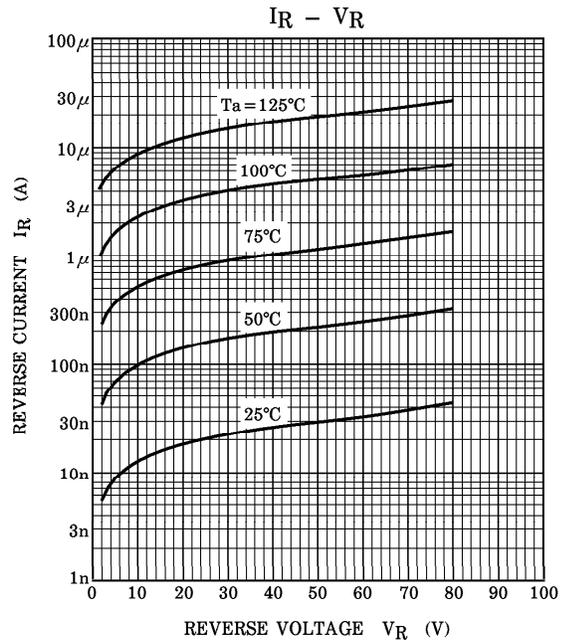
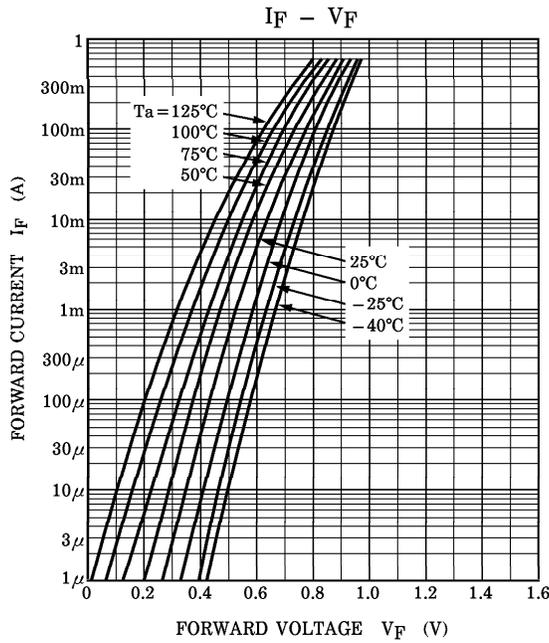
Weight : 0.012g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_F(1)$	$I_F = 10mA$	—	0.64	—	V
	$V_F(2)$	$I_F = 100mA$	—	0.78	—	
	$V_F(3)$	$I_F = 200mA$	—	0.84	1.2	
Reverse Current	$I_R(1)$	$V_R = 30V$	—	—	0.25	μA
	$I_R(2)$	$V_R = 80V$	—	—	0.50	
Total Capacitance	C_T	$V_R = 0, f = 1MHz$	—	7	—	pF
Reverse Recovery Time	t_{rr}	$I_F = 30mA, Fig.1$	—	7	20	ns

Fig.1 REVERSE RECOVERY TIME (t_{rr}) TEST CIRCUIT





● The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.

● The information contained herein is subject to change without notice.